

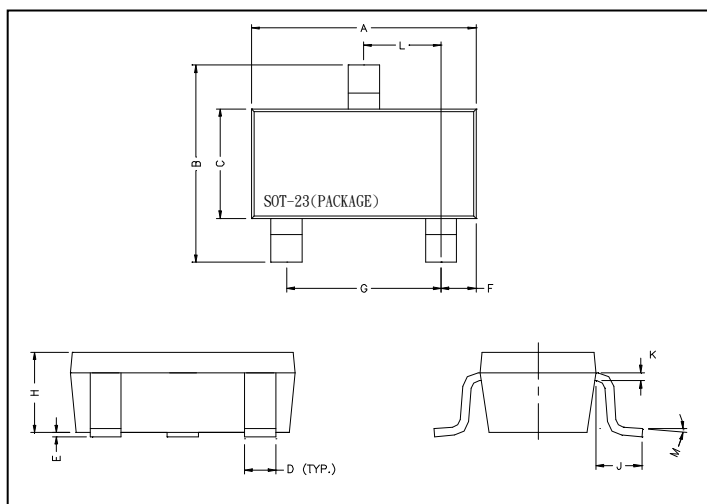
## G425SD

**SURFACE MOUNT, SCHOTTKY BARRIER DIODE**  
**VOLTAGE 40V, CURRENT 0.1A**

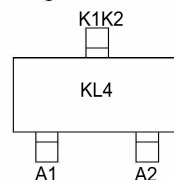
### Description

The G425SD is designed for low power rectification.

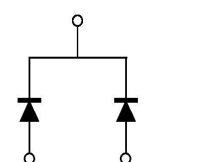
### Package Dimensions



Marking:



Circuit :



| REF. | Millimeter |      | REF. | Millimeter |      |
|------|------------|------|------|------------|------|
|      | Min.       | Max. |      | Min.       | Max. |
| A    | 2.70       | 3.10 | G    | 1.90       | REF. |
| B    | 2.40       | 2.80 | H    | 1.00       | 1.30 |
| C    | 1.40       | 1.60 | K    | 0.10       | 0.20 |
| D    | 0.35       | 0.50 | J    | 0.40       | -    |
| E    | 0          | 0.10 | L    | 0.85       | 1.15 |
| F    | 0.45       | 0.55 | M    | 0°         | 10°  |

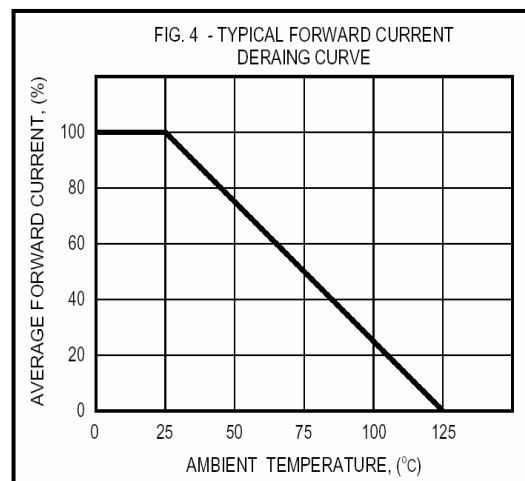
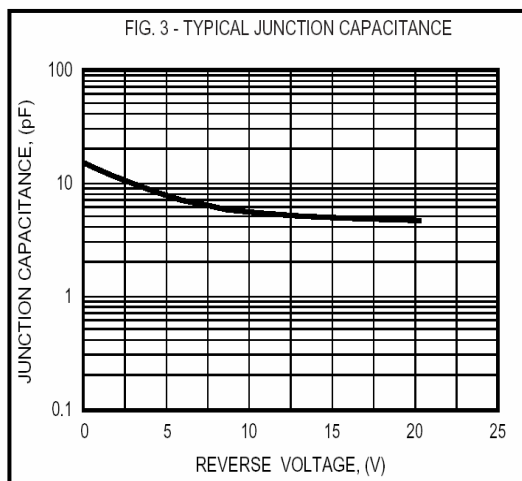
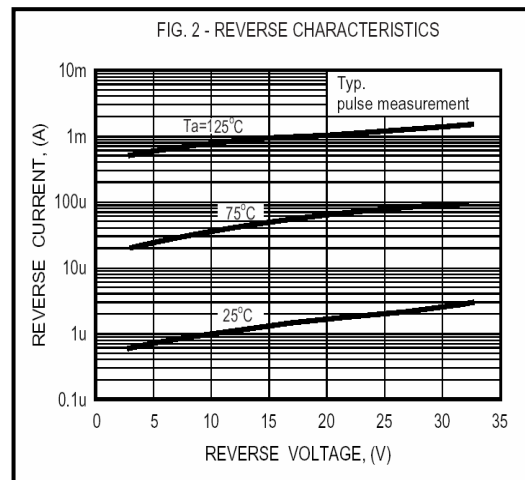
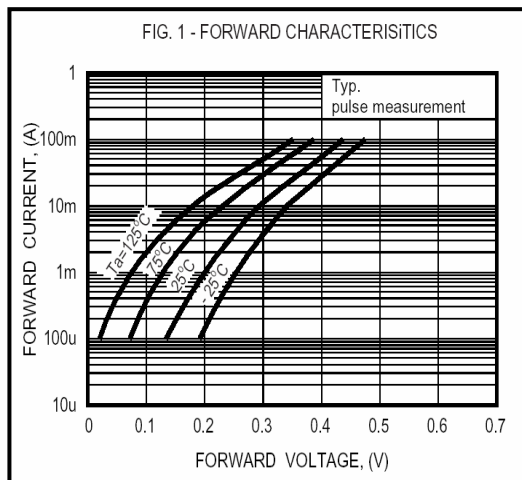
### Absolute Maximum Ratings at Ta = 25°C

| Parameter                                                   | Symbol           | Ratings    | Unit |
|-------------------------------------------------------------|------------------|------------|------|
| Junction Temperature                                        | T <sub>j</sub>   | +125       | °C   |
| Storage Temperature                                         | T <sub>stg</sub> | -40 ~ +125 | °C   |
| Maximum Recurrent Peak Reverse Voltage                      | V <sub>RRM</sub> | 40         | V    |
| Maximum RMS Voltage                                         | V <sub>RMS</sub> | 28         | V    |
| Maximum DC Blocking Voltage                                 | V <sub>DC</sub>  | 40         | V    |
| Peak Forward Surge Current at 8.3mSec single half sine-wave | I <sub>FSM</sub> | 1.0        | A    |
| Typical Junction Capacitance between Terminal               | C <sub>J</sub>   | 6.0        | pF   |
| Maximum Average Forward Rectified Current                   | I <sub>o</sub>   | 0.1        | A    |
| Total Power Dissipation                                     | PD               | 225        | mW   |

### Characteristics at Ta = 25°C

| Characteristics                       | Symbol            | Typ. | Unit | Test Condition            |
|---------------------------------------|-------------------|------|------|---------------------------|
| Maximum Instantaneous Forward Voltage | V <sub>F(1)</sub> | 0.55 | V    | I <sub>F(1)</sub> = 100mA |
| Maximum Instantaneous Forward Voltage | V <sub>F(2)</sub> | 0.34 | V    | I <sub>F(2)</sub> = 10mA  |
| Maximum Average Reverse Current       | I <sub>R</sub>    | 30   | uA   | V <sub>R</sub> = 10V      |

## Characteristics Curve



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